Preliminary

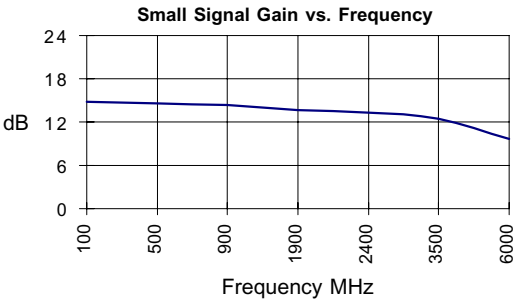
SGA-3263

DC-3600 MHz Silicon Germanium HBT Cascadeable Gain Block

Product Description

Stanford Microdevices' SGA-3263 is a high performance cascadeable 50-ohm amplifier designed for operation at voltages as low as 2.6V. This RFIC uses the latest Silicon Germanium Heterostructure Bipolar Transistor (SiGe HBT) process featuring 1 micron emitters with F_T up to 50 GHz.

This circuit uses a darlington pair topology with resistive feedback for broadband performance as well as stability over its entire temperature range. Internally matched to 50 ohm impedance, the SGA-3263 requires only DC blocking and bypass capacitors for external components.



Product Features

- **DC-3600 MHz Operation**
- **Single Voltage Supply**
- **High Output Intercept: +26.2dBm typ. at 850 MHz**
- **Low Current Draw: 35mA at 2.6V typ.**
- **Low Noise Figure: 3.6dB typ. at 850 MHz**

Applications

- **Oscillator Amplifiers**
- **Cordless Phones**
- **IF/ RF Buffer Amplifier**
- **Drivers for CATV Amplifiers**

Symbol	Parameters: Test Conditions: Z_0 = 50 Ohms, Id = 35 mA, T = 25°C		Units	Min.	Typ.	Max.
P_{1dB}	Output Power at 1dB Compression	f = 850 MHz f = 1950 MHz	dBm dBm		11.6 10.9	
S_{21}	Small Signal Gain	f = DC - 1000 MHz f = 1000 - 2000 MHz f = 2000 - 3600 MHz	dB dB dB	13.1	14.6 13.9 12.6	
S_{12}	Reverse Isolation	f = DC - 1000 MHz f = 1000 - 2000 MHz f = 2000 - 3600 MHz	dB dB dB		18.3 18.7 19.0	
S_{11}	Input VSWR	f = DC - 2400 MHz f = 2400 - 3600 MHz	-		1.2:1 1.2:1	
S_{22}	Output VSWR	f = DC - 2400 MHz f = 2400 - 3600 MHz	-		1.1:1 1.2:1	
IP_3	Third Order Intercept Point Power out per Tone = -5 dBm	f = 850 MHz f = 1950 MHz	dBm dBm		26.2 24.1	
NF	Noise Figure	f = DC - 1000 MHz f = 1000 - 2400 MHz	dB dB		3.6 3.9	
T_D	Group Delay	f = 1000 MHz	pS		99	
V_D	Device Voltage		V	2.3	2.6	2.9

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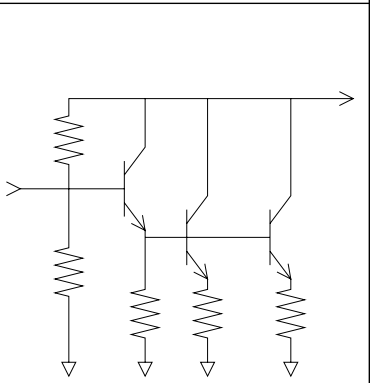
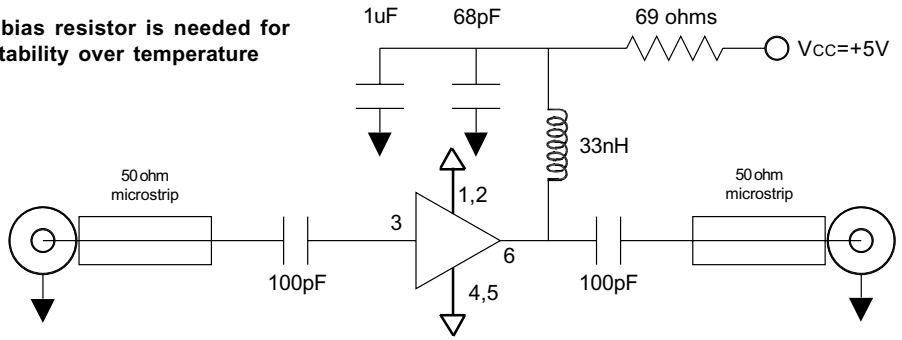
Parameter	Specification				Test Condition
	Min	Typ.	Max.	Unit	
Bandwidth					T= 25C
Frequency Range	DC		3600	MHz	
Device Bias					T= 25C
Operating Voltage		2.6		V	
Operating Current		35		mA	
500 MHz					T= 25C
Gain		14.6		dB	
Noise Figure		3.7		dB	
Output IP3		26.1		dBm	
Output P1dB		11.4		dBm	
Input Return Loss		24.8		dB	
Isolation		18.3		dB	
850 MHz					T= 25C
Gain		14.4		dB	
Noise Figure		3.6		dB	
Output IP3		26.2		dBm	
Output P1dB		11.6		dBm	
Input Return Loss		24.0		dB	
Isolation		18.4		dB	
1950 MHz					T= 25C
Gain		13.6		dB	
Noise Figure		3.8		dB	
Output IP3		24.1		dBm	
Output P1dB		10.9		dBm	
Input Return Loss		22.5		dB	
Isolation		18.9		dB	
2400 MHz					T= 25C
Gain		13.3		dB	
Noise Figure		4.3		dB	
Output IP3		22.6		dBm	
Output P1dB		10.1		dBm	
Input Return Loss		20.3		dB	
Isolation		19.0		dB	

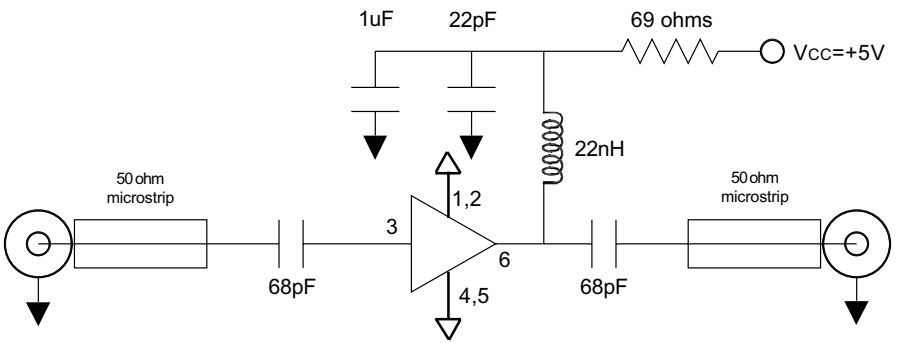
Pin #	Function	Description	Device Schematic
1	GND	Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.	
2	GND	Sames as Pin 1	
3	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.	
4	GND	Sames as Pin 1	
5	GND	Sames as Pin 1	
6	RF OUT	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.	

Application Schematic for +5V Operation at 900 MHz

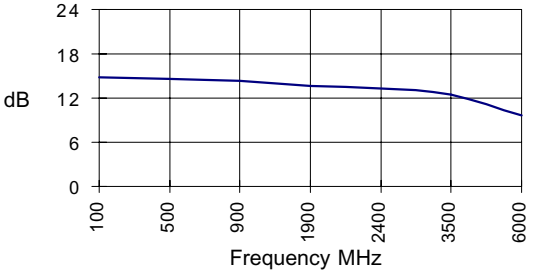
Note: A bias resistor is needed for stability over temperature



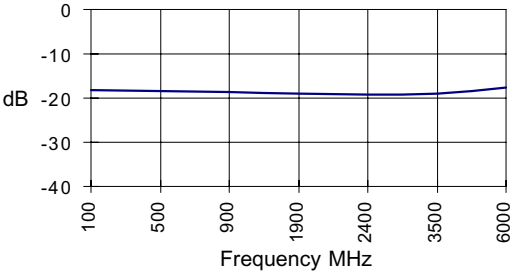
Application Schematic for +5V Operation at 1900 MHz



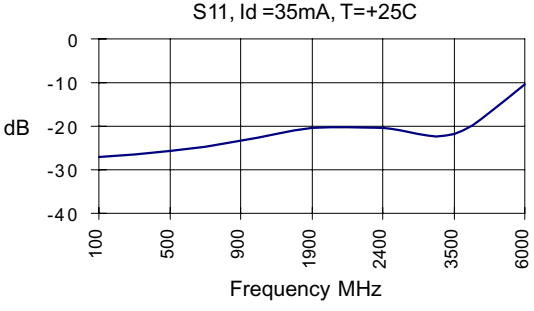
S21, Id =35mA, T=+25C



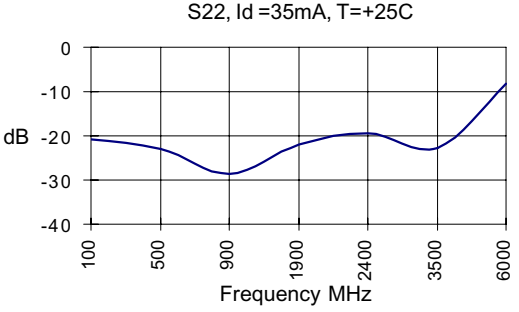
S12, Id =35mA, T=+25C



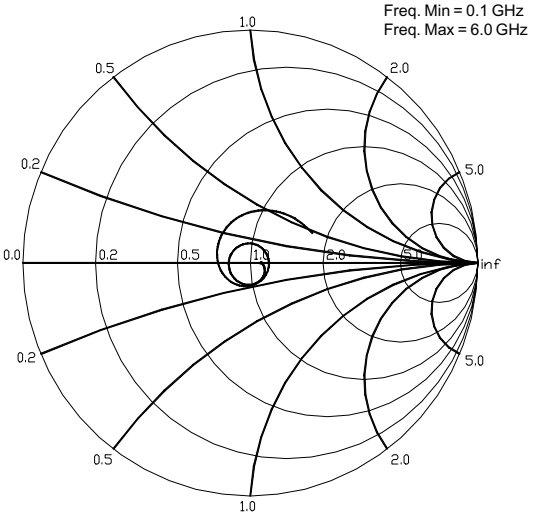
S11, Id =35mA, T=+25C



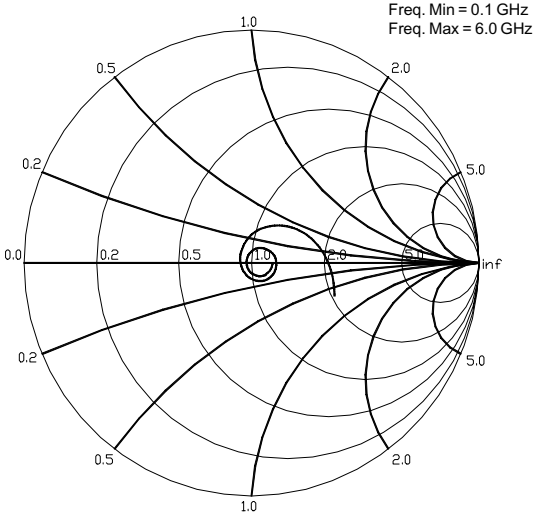
S22, Id =35mA, T=+25C



S11, Id=35mA, Ta= +25C



S22, Id=35mA, Ta= +25C



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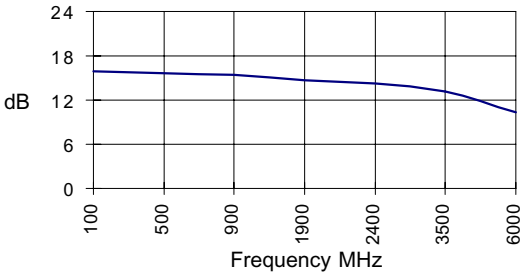
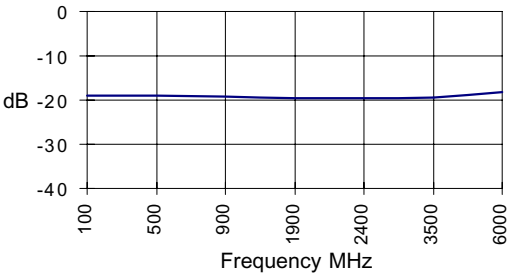
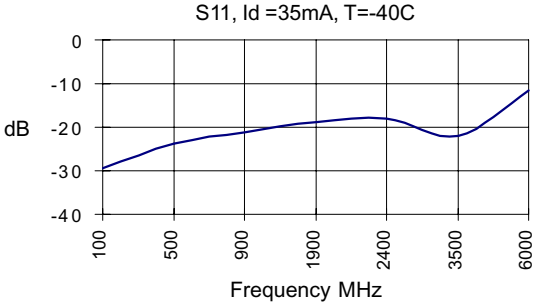


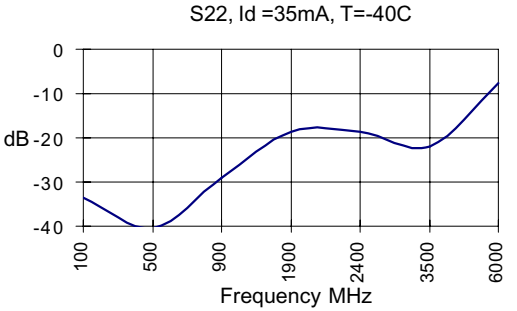
S12, Id =35mA, T=-40C



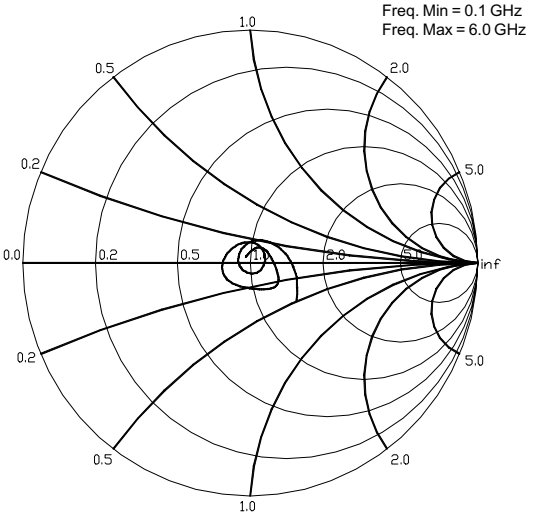
S11, Id =35mA, T=-40C



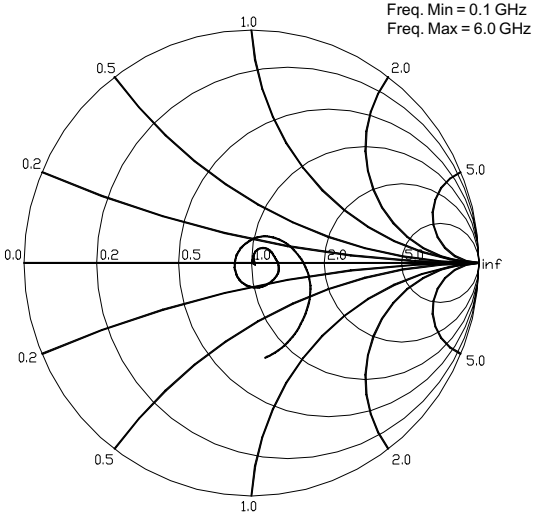
S22, Id =35mA, T=-40C



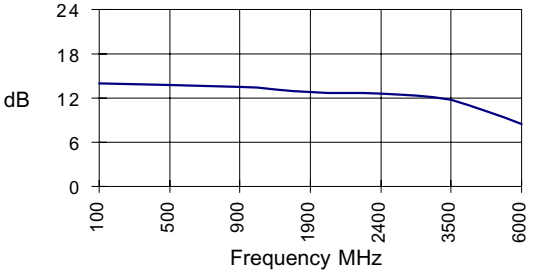
S11, Id=35mA, T=-40C



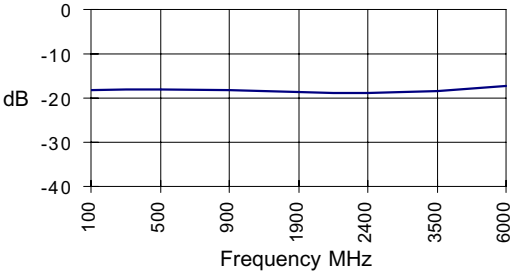
S22, Id=35mA, T=-40C



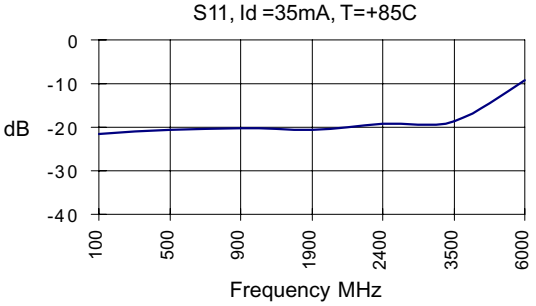
S21, Id =35mA, T=+85C



S12, Id =35mA, T=+85C



S11, Id =35mA, T=+85C



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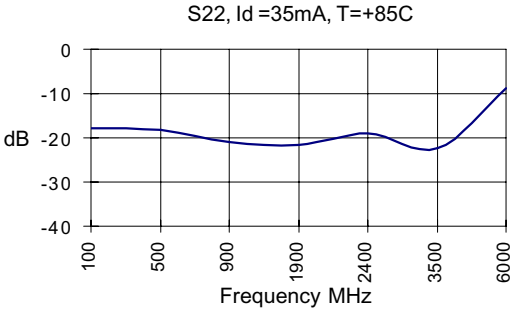
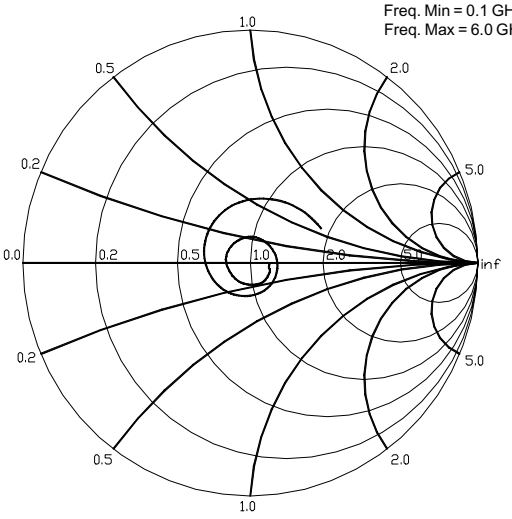


S11, Id=35mA, T=+85C



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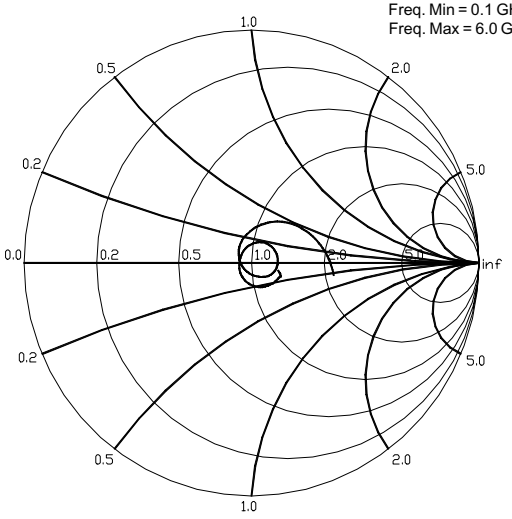


SGA-3263 DC-3600 MHz 2.6V SiGe Amplifier

Absolute Maximum Ratings

Parameter	Value	Unit
Supply Current	70	mA
Operating Temperature	-40 to +85	C
Maximum Input Power	+5	dBm
Storage Temperature Range	-40 to +85	C
Operating Junction Temperature	+125	C

Caution:

Operation of this device above any one of these parameters may cause permanent damage. Appropriate precautions in handling, packaging and testing devices must be observed.

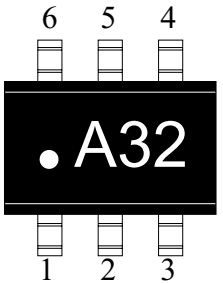
Thermal Resistance (Lead-Junction): 255° C/W

Part Number Ordering Information

Part Number	Reel Size	Devices/Reel
SGA-3263-TR1	7"	3000

Recommended Bias Resistor Values					
Supply Voltage(Vs)	4V	5V	7.5V	9V	12V
Rbias (Ohms)	40	69	140	183	269

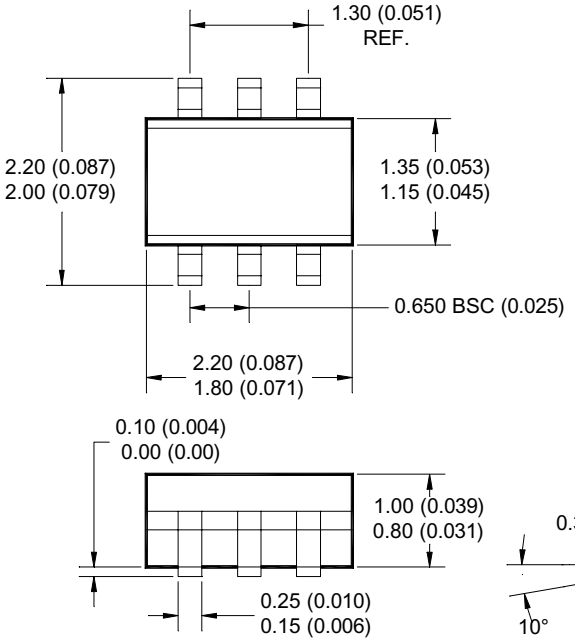
Package Marking



Pin Designation	
1	GND
2	GND
3	RF in
4	GND
5	GND
6	RF out

Note: Pin 1 is on lower left when you can read package marking

Package Dimensions



Pad Layout